

In the Specification:

Please amend the paragraph on Page 4, lines 28-31 as follows:

Further, FIG. 3 is a graph illustrating breakdown voltage characteristics of a high voltage device  $\text{E} \underline{\text{D}}$  in which the gate electrode is formed using the polysilicon film formed while applying evaporation, and a high voltage device  $\text{D} \underline{\text{C}}$  in which a gate electrode is formed using a polysilicon film that is formed without applying vacuum.